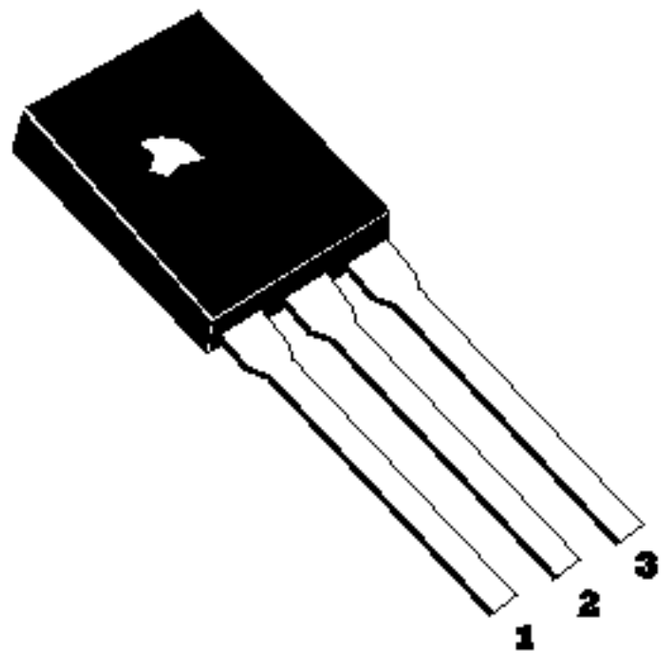
MJ13001AL

NPN TRIPLE DIFFUSED SILICON TRANSISTOR

HIGH VOLTAGE TRANSISTOR

* Collector-Emitter Voltage Vceo=400V
* Collector Dissipation Pc(Max)=1W (Ta=25°C)

Package: TO-126



PIN: / STYLE	1	2	3
NO.1	E	C	B

ABSOLUTE MAXIMUM RATINGS at Tamb=25°C

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	500	V
Collector-Emitter Voltage	Vceo	400	V
Emitter-Base Voltage	Vebo	8	V
Collector Current	Ic	500	mA
Collector Dissipation	Pc	1	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~150	°C

ELECTRICAL CHARACTERISTICS at Tamb=25°C

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVcbo	500			V	Ic=100uA Ie=0
Collector-Emitter Breakdown Voltage	BVceo	400			V	Ic=1mA Ib=0
Emitter-Base Breakdown Voltage	BVebo	8			V	Ie=100uA Ic=0
Collector Cutoff Current	Icbo			10	uA	Vcb=420V Ie=0
Emitter Cutoff Current	Iebo			10	uA	Veb=8V Ic=0
DC Current Gain	Hfe	8		40		Vce=10V Ic=5mA
Collector-Emitter Saturation Voltage	Vce(sat)			0.4	V	Ic=50mA Ib=10mA
Base-Emitter Saturation Voltage	Vbe(sat)			1	V	Ic=50mA Ib=10mA
Current Gain-Bandwidth product	fT	10			MHz	Vce=10V Ic=10mA
						f=1MHz